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OPEN Author Correction: High-quality AIN grown with a single substrate temperature below 1200 °C

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Kapil Gupta was omitted from the author list in the original version of this Article. This has been corrected in the PDF and HTML versions of the Article, and in the accompanying Supplementary Information file.

The Author Contributions section now reads:

C.P.H. ran the MOCVD growth, performed AFM, SEM and XRD measurements, and wrote the paper. K.G., C.H.W. and C.P.L. carried out the TEM characterization. K.Y.L. directed the research and wrote the paper. All authors reviewed the manuscript.

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